



<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND OTHER DOCUMENTS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	<b>ATTY. DOCKET NO.</b> 0180151	<b>SERIAL NO.</b> 10/705,347
	<b>APPLICANTS:</b> Labelle, et al.	
	<b>FILING DATE:</b> November 8, 2003	<b>GROUP ART:</b> Unknown

U.S. PATENT DOCUMENTS							
Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
KCC	1	2003/0218223 A1	11/27/2003	Nishiyama, et al.	—	—	—
KCC	2	2003/0119334 A1	6/26/2003	Kwak, et al.	—	—	—
KCC	3	5,344,522	9/6/1994	Yagi, et al.	—	—	—
KCC	4	6,159,849	12/12/2000	Kang, et al.	—	—	—

FOREIGN PATENT DOCUMENTS								
Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
KCC	1	JP 2003/249649 A	9/5/2003	Japan	—	—	abstract	only
KCC	2	JP 2003/008005 A	1/10/2003	Japan	—	—	abstract	only
KCC	3	JP 06350093 A	12/22/1994	Japan	—	—	abstract	only
KCC	4	JP 08316466 A	11/29/1996	Japan	—	—	abstract	only

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
KCC	1	Cho et al, <i>Novel Nitrogen Profile Engineering for Improved TaN/HfO<sub>2</sub>/Si MOSFET Performance</i> , IEEE, 655-658 (December, 2001)
KCC	2	Choi et al, <i>High-Quality Ultra-thin HfO<sub>2</sub> Gate Dielectric MOSFETs with TaN Electrode and Nitridation Surface Preparation</i> , Digest of Technical Papers, JSAP, 15-16 (2001)

<b>EXAMINER:</b> KCC [Signature]	<b>DATE CONSIDERED:</b> 8-1-05
<b>EXAMINER:</b> Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant. <b>Information Disclosure Statement-- Section 9 PTO-1449</b>	